

MOSFET - Power, Single N-Channel, SO8-FL

40 V, 0.57 mΩ, 380 A

NTMFS0D6N04XM

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Small Footprint (5x6 mm) with Compact Design
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Motor Drive
- Battery Protection
- ORing

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	DC V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	380
		$T_C = 100^\circ\text{C}$	268
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	150
Continuous Drain Current $R_{\theta JA}$	I_{DA}	$T_A = 25^\circ\text{C}$	61
		$T_A = 100^\circ\text{C}$	43
Pulsed Drain Current	$T_C = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$	I_{DM}	2801
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	125	A
Single Pulse Avalanche Energy ($I_{PK} = 24.9 \text{ A}$)	E_{AS}	562	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

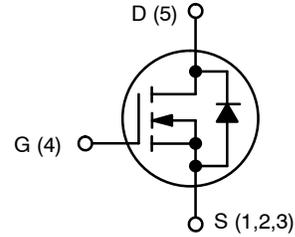
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

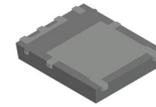
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	1	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Notes 1, 2)	$R_{\theta JA}$	38.8	

1. Surface-mounted on FR4 board using 650 mm², 2 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	0.57 mΩ @ 10 V	380 A

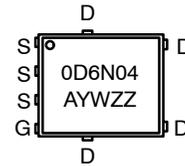


N-CHANNEL MOSFET



DFN5 (SO8-FL)
CASE 506FA

MARKING DIAGRAM



0D6N04 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NTMFS0D6N04XM

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}, \text{Referenced to } 25^\circ\text{C}$		15		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, T_J = 25^\circ\text{C}$			10	μA
		$V_{DS} = 40\text{ V}, T_J = 125^\circ\text{C}$			100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 25^\circ\text{C}$		0.51	0.57	m Ω
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 210\text{ }\mu\text{A}, T_J = 25^\circ\text{C}$	2.5	3	3.5	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 210\text{ }\mu\text{A}$		-7.26		mV/ $^\circ\text{C}$
Forward Trans-conductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 30\text{ A}$		175		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		5574		pF
Output Capacitance	C_{OSS}			3887		
Reverse Transfer Capacitance	C_{RSS}			79.5		
Total Gate Charge	$Q_G(TOT)$	$V_{DD} = 20\text{ V}, I_D = 50\text{ A}, V_{GS} = 10\text{ V}$		86.4		nC
Threshold Gate Charge	$Q_G(TH)$			16.3		
Gate-to-Source Charge	Q_{GS}			24.5		
Gate-to-Drain Charge	Q_{GD}			15.7		
Gate Resistance	R_G	$f = 1\text{ MHz}$		5.31		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}, V_{DD} = 20\text{ V}, I_D = 50\text{ A}, R_G = 0\text{ }\Omega$		33.9		ns
Rise Time	t_r			15.6		
Turn-Off Delay Time	$t_{d(OFF)}$			58.2		
Fall Time	t_f			15.3		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$I_S = 30\text{ A}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$		0.78	1.2	V
		$I_S = 30\text{ A}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$		0.63		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_S = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 20\text{ V}$		77.4		ns
Charge Time	t_a			41		
Discharge Time	t_b			36.5		
Reverse Recovery Charge	Q_{RR}			162		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NTMFS0D6N04XM

TYPICAL CHARACTERISTICS

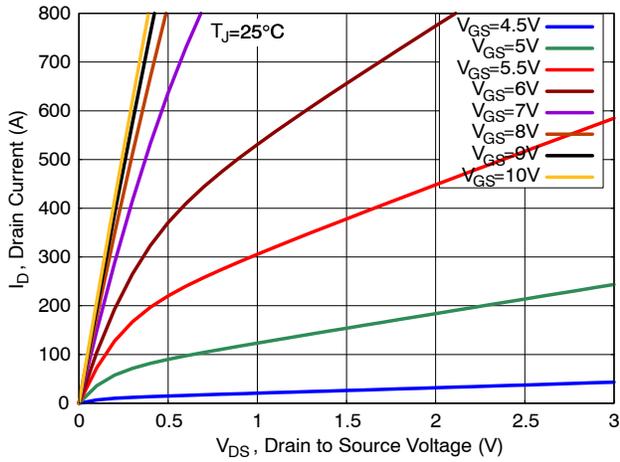


Figure 1. On-Region Characteristics

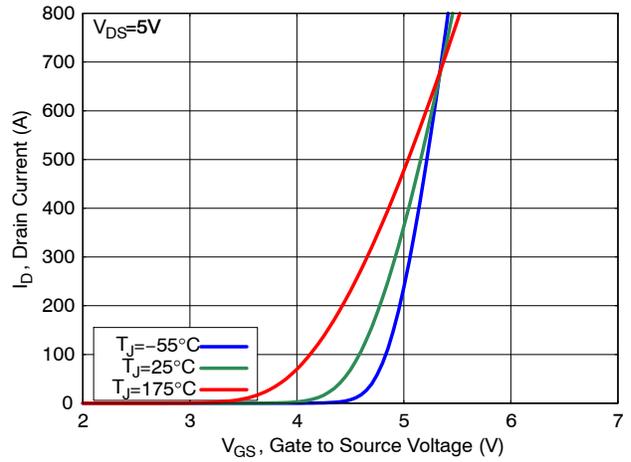


Figure 2. Transfer Characteristics

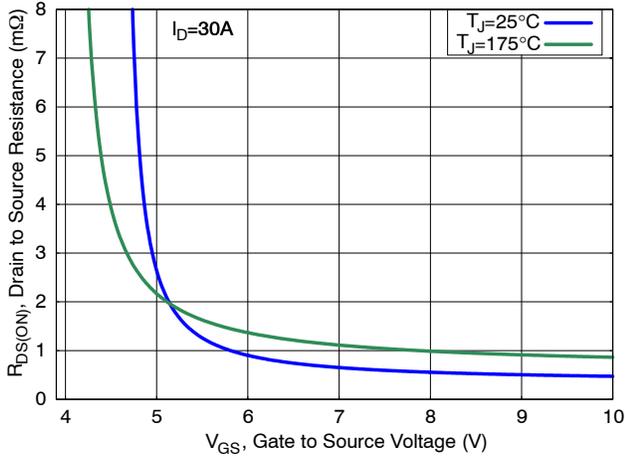


Figure 3. On-Resistance vs. Gate Voltage

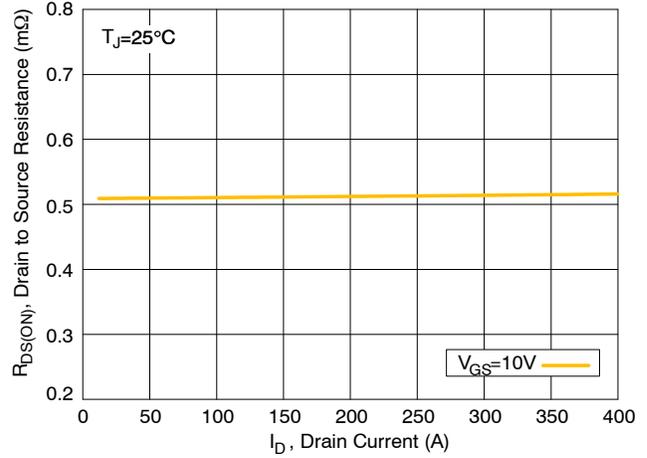


Figure 4. On-Resistance vs. Drain Current

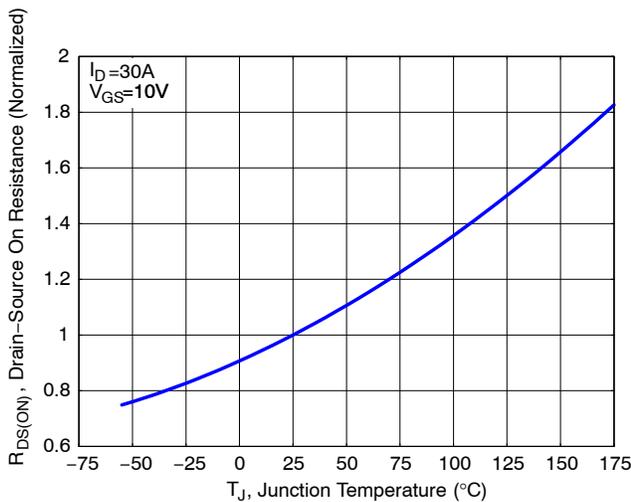


Figure 5. Normalized ON Resistance vs. Junction Temperature

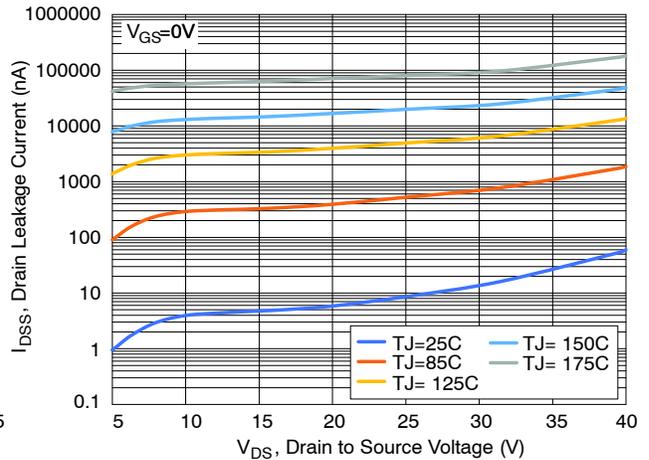


Figure 6. Drain to Source Voltage vs. Drain Leakage

NTMFS0D6N04XM

TYPICAL CHARACTERISTICS (Continued)

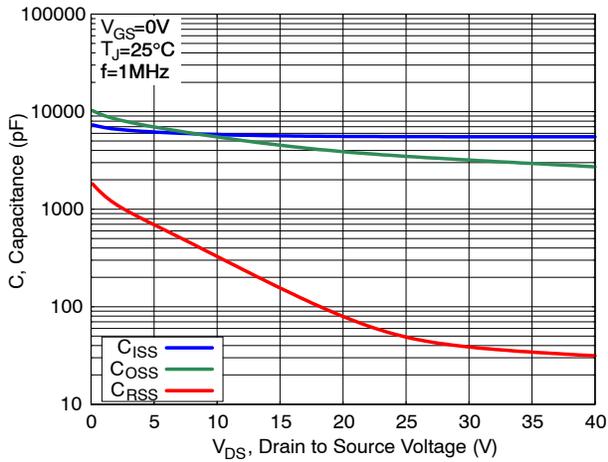


Figure 7. Capacitance Characteristics

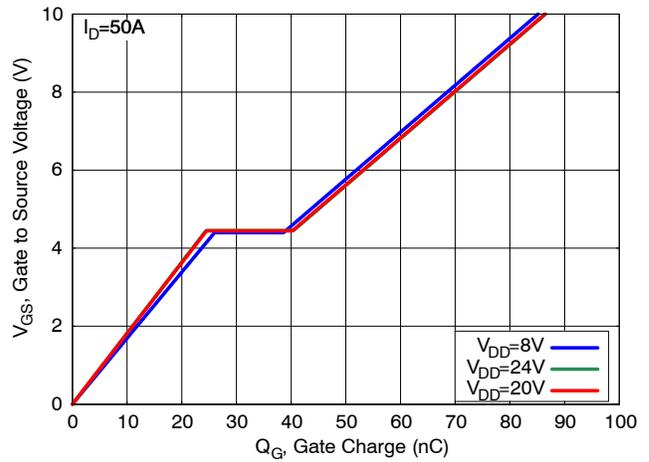


Figure 8. Gate Charge Characteristics

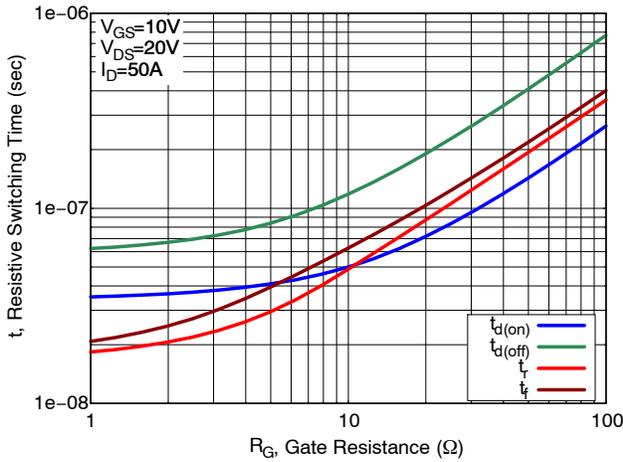


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

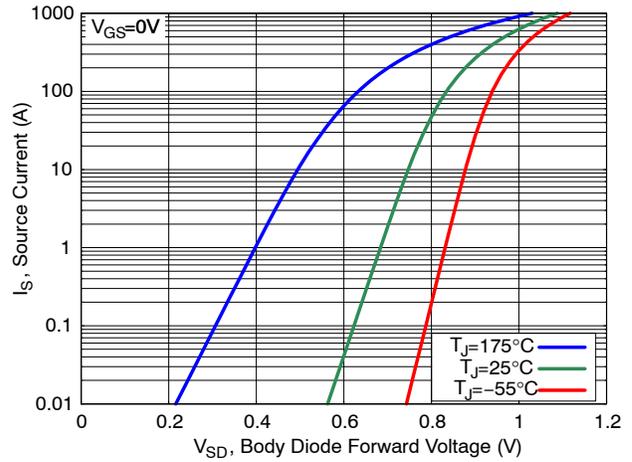


Figure 10. Diode Forward Characteristics

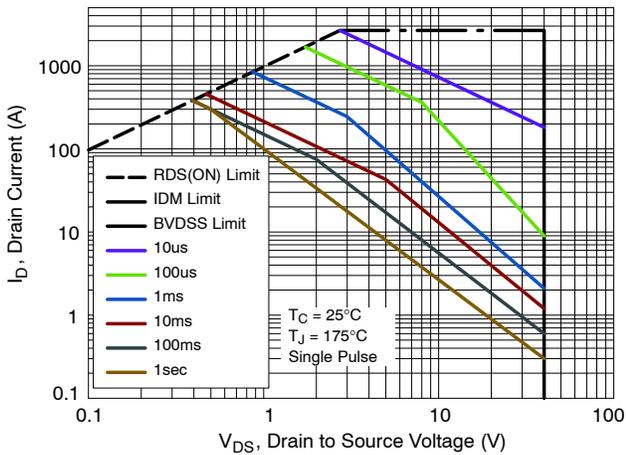


Figure 11. Safe Operating Area (SOA)

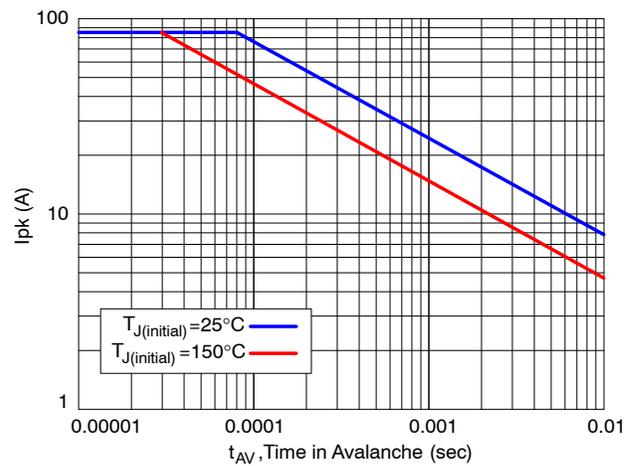


Figure 12. Avalanche Current vs. Pulse Time (UIS)

NTMFS0D6N04XM

TYPICAL CHARACTERISTICS (Continued)

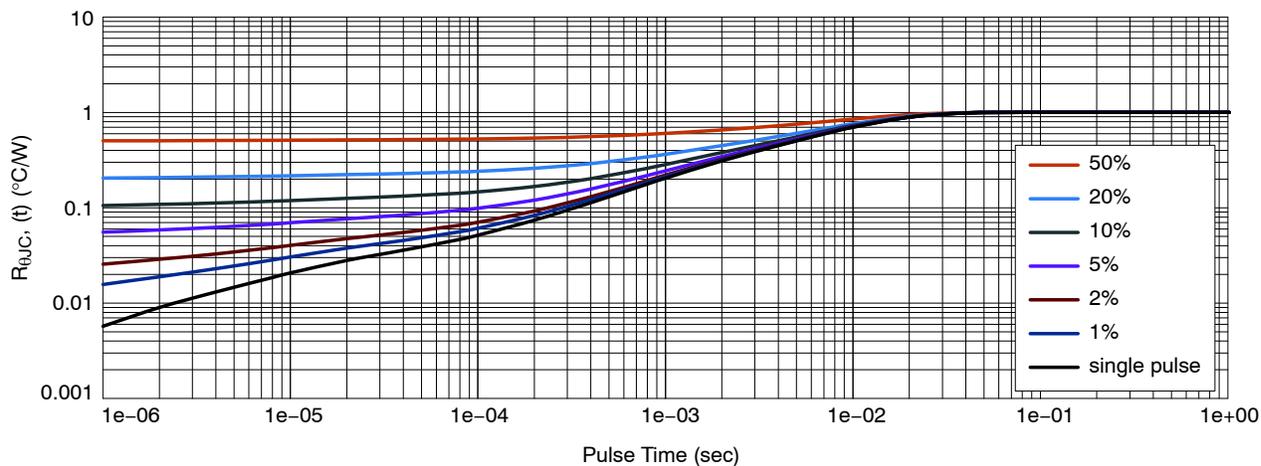


Figure 13. Thermal Response

DEVICE ORDERING INFORMATION

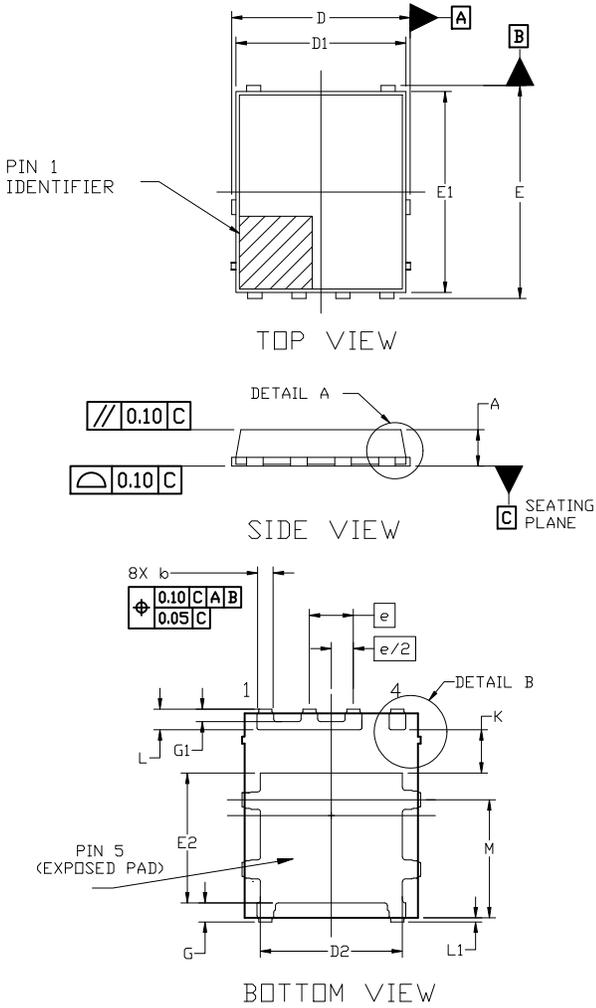
Device	Marking	Package	Shipping [†]
NTMFS0D6N04XMT1G	0D6N04	DFN5 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTMFS0D6N04XM

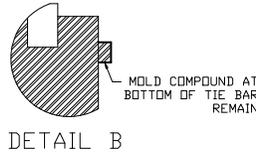
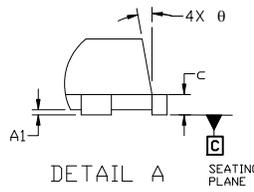
PACKAGE DIMENSIONS

DFN5 5x6, 1.27P
CASE 506FA
ISSUE O

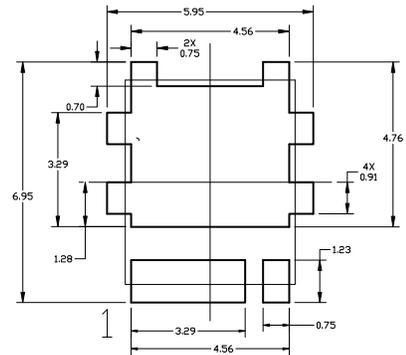


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.80	5.00	5.20
D2	3.90	4.10	4.30
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.55	3.75	3.95
e	1.27 BSC		
G	0.50	0.55	0.70
G1	0.26	0.36	0.46
k	1.10	1.25	1.40
L	0.50	0.60	0.70
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



RECOMMENDED MOUNTING FOOTPRINT

- * For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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